

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings of claims in the application:

**Listing of Claims:**

1                    1.        (Currently amended): An electronic device comprising a  
2        semiconductor device provided with pads and a substrate provided with pads on which  
3        ~~substrate~~ said semiconductor device is mounted, the pads of the semiconductor device  
4        being bonded to the pads of the substrate through junctions each including Cu balls and  
5        Cu-Sn compounds containing  $\text{Cu}_6\text{Sn}_5$ , said Cu balls being bonded to each other by said  
6        Cu-Sn compounds.

1                    2.        (Original): An electronic device according to claim 1, wherein  
2        each of said junctions contains at least one kind selected from the group consisting of In,  
3        Zn and Bi.

1                    3.        (Original): An electronic device according to claim 2, wherein  
2        each of said junctions has plastic balls.

1                    4.        (Withdrawn): An electronic device comprising a semiconductor  
2        device provided with pads and a substrate provided with pads on which substrate said  
3        semiconductor device is mounted, said pads of said semiconductor device being bonded  
4        to said pads of said substrate through solder portions each having Cu balls each surface of  
5        which is plated with one selected from the group consisting of Sn and a Sn-base alloy.

1                    5.        (Withdrawn): An electronic device comprising a semi-conductor  
2        device provided with pads and a substrate provided with pads on which substrate said  
3        semiconductor device is mounted, said pads of said semiconductor device being bonded  
4        to said pads of said substrate through solder portions each having Cu balls and solder  
5        balls, a weight ratio of said solder balls to said Cu balls being in a range of 0.6 to 1.4.

1                   6.       (Withdrawn): An electronic device according to claim 5, wherein  
2 said solder balls are one kind selected from the group consisting of eutectic Sn-Cu-base  
3 solder balls, eutectic Sn-Ag-base solder balls and eutectic Sn-Ag-Cu-base solder balls.

1                   7.       (Withdrawn): An electronic device according to claim 4 or 5,  
2 wherein at least one kind selected from the group consisting of In, Zn and Bi is added to  
3 said solder portions.

1                   8.       (Withdrawn): An electronic device according to claim 4 or 5,  
2 wherein said solder has plastic balls.

1                   9.       (Withdrawn): An electronic device according to claim 4 or 5,  
2 wherein said solder portions include particles of at least one kind selected from the group  
3 consisting of invar, silica, alumina, AlN and SiC.

1                   10.     (Currently amended): An electronic device comprising a  
2 semiconductor device provided with pads, a first substrate provided with pads on which  
3 ~~substrate~~ said semiconductor device is mounted, and a second substrate provided with  
4 pads on which ~~second substrate~~ said first substrate is mounted,  
5                   said pads of the semiconductor device being bonded to said pads of the  
6 first substrate through junctions each including Cu balls and a Cu<sub>6</sub>Sn<sub>5</sub> compound, said Cu  
7 balls being bonded to each other by said Cu<sub>6</sub>Sn<sub>5</sub> compound,  
8                   said pads of the first substrate being bonded to said pads of the second  
9 substrate by ~~one a solder~~ a solder selected from the group consisting of a Sn-Ag-base solder, a Sn-  
10 Ag-Cu-base solder, and a Sn-Cu-base solder ~~and a Sn-Zn base solder~~.

1                   11.     (Withdrawn): An electronic device comprising a semiconductor  
2 device provided with pads, a first substrate provided with pads on which substrate said  
3 semiconductor device is mounted, and a second substrate provided with pads on which  
4 second substrate said first substrate is mounted,

5                   said pads of the semiconductor device being bonded to said pads of  
6 the first substrate through solder portions each including Cu balls each surface of which  
7 is plated with one selected from the group consisting of Sn and a Sn alloy,  
8                   said pads of the first substrate being bonded to said pads of the  
9 second substrate by one selected from the group consisting of a Sn-Ag-base solder, a Sn-  
10 Ag-Cu-base solder, a Sn-Cu-base solder and a Sn-Zn-base solder

1                   12.     (Withdrawn): An electronic device comprising a semiconductor  
2 device provided with pads, a first substrate provided with pads on which substrate said  
3 semiconductor device is mounted, and a second substrate provided with pads on which  
4 second substrate said first substrate is mounted,  
5                   said pads of the semiconductor device being bonded to said pads of  
6 the first substrate through solder portions each including Cu balls and solder balls, a  
7 weight ratio of said solder balls to said Cu balls being in a range of 0.6 to 1.4,  
8                   said pads of the first substrate being bonded to said pads of the  
9 second substrate by one selected from the group consisting of a Sn-Ag-base solder, a Sn-  
10 Ag-Cu-base solder, a Sn-Cu-base solder and a Sn-Zn-base solder.

1                   13.     (Withdrawn): An electronic device according to any one of claims  
2 10 to 12, said pads of the first substrate being bonded to said pads of the second substrate  
3 by a Sn-(2.0 to 3.5) Ag-(0.5 to 1.0) Cu solder.

1                   14.     (Currently amended): An electronic device comprising a  
2 semiconductor chip provided on one face thereof with connection terminals, and a  
3 substrate provided with connection terminals on which ~~substrate~~ said semiconductor chip  
4 is mounted,  
5                   said connection terminals of said substrate and said connection terminals  
6 of said semiconductor chip are bonded to each other by wire bonding,

7 another face of said semiconductor chip and said substrate being bonded  
8 to each other through a bonding portion ~~portions each~~ containing Cu balls and Cu<sub>6</sub>Sn<sub>5</sub>  
9 compounds, said Cu balls being bonded to each other by said Cu<sub>6</sub>Sn<sub>5</sub> compounds.

1 15. (Currently amended): An electronic device according to claim 14,  
2 said substrate comprising external connection terminals on a rear face regarding a face  
3 provided with said connection terminals, said external connection terminals being formed  
4 of at least one solder selected from the group consisting of a Sn-Ag-based solder, a Sn-  
5 Ag-Cu-based solder, and a Sn-Cu base solder ~~and a Sn-Zn-based solder~~.

1 16. (New): An electronic device according to claim 1, wherein said  
2 junctions are formed by using a solder having Cu balls each surface of which is plated  
3 with Sn or a Sn alloy.

1 17. (New): An electronic device according to claim 1, wherein said  
2 junctions are formed by using a solder having Cu balls and solder balls.

1 18. (New): An electronic device according to claim 17, wherein said  
2 solder balls are Sn solder balls, eutectic Sn-Cu solder balls, eutectic Sn-Ag solder balls or  
3 Eutectic Sn-Ag-Cu solder balls.

1 19. (New): An electronic device according to claim 16, wherein at  
2 least one of In, Zn and Bi is added to said solder.

1 20. (New): An electronic device according to claim 17, wherein at  
2 least one of In, Zn and Bi is added to said solder.

1 21. (New): An electronic device according to claim 10, wherein said  
2 junctions are formed by using a solder having Cu balls each surface of which is plated  
3 with Sn or a Sn alloy.

1                   22.   (New): An electronic device according to claim 10, wherein said  
2 junctions are formed by using a solder having Cu balls and solder balls.

1                   23.   (New): An electronic device according to claim 22, wherein said  
2 solder balls are Sn solder balls, eutectic Sn-Cu solder balls, eutectic Sn-Ag solder balls or  
3 Eutectic Sn-Ag-Cu solder balls.

1                   24.   (New): An electronic device according to claim 14, wherein said  
2 junctions are formed by using a solder having Cu balls each surface of which is plated  
3 with Sn or a Sn alloy.

1                   25.   (New): An electronic device according to claim 14, wherein said  
2 junctions are formed by using a solder having Cu balls and solder balls.

3                   26.   (New): An electronic device according to claim 25, wherein said  
4 solder balls are Sn solder balls, eutectic Sn-Cu solder balls, eutectic Sn-Ag solder balls or  
5 Eutectic Sn-Ag-Cu solder balls.